

GTM CORPORATION

ISSUED DATE :2006/08/16
REVISED DATE :

GJ55N03

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

BVDSS	25V
RDS(ON)	6mΩ
Id	55A

Description

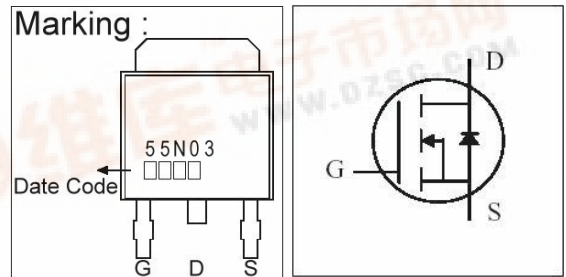
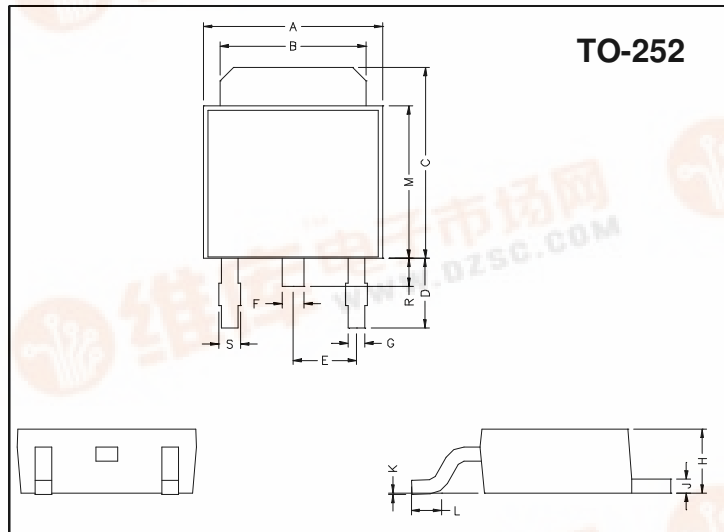
The GJ55N03 provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-252 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

Features

- *Dynamic dv/dt Rating
- *Simple Drive Requirement
- *Repetitive Avalanche Rated
- *Fast Switching

Package Dimensions



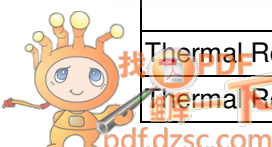
REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.40	3.00	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current, $V_{GS}@10V$	$I_D @T_C=25^{\circ}C$	55	A
Continuous Drain Current, $V_{GS}@10V$	$I_D @T_C=100^{\circ}C$	35	A
Pulsed Drain Current ¹	I_{DM}	215	A
Total Power Dissipation	$P_D @T_C=25^{\circ}C$	62.5	W
Linear Derating Factor		0.5	W/°C
Single Pulse Avalanche Energy ²	E_{AS}	240	mJ
Single Pulse Avalanche Current	I_{AS}	31	A
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-case	R_{thj-c}	2.0	°C/W
Thermal Resistance Junction-ambient	R_{thj-a}	110	°C/W



Electrical Characteristics (T_j = 25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	25	-	-	V	V _{GS} =0, I _D =250uA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_j$	-	0.037	-	V/°C	Reference to 25°C, I _D =1mA
Gate Threshold Voltage	V _{GS(th)}	1.0	-	3.0	V	V _{DS} =V _{GS} , I _D =250uA
Forward Transconductance	g _{fs}	-	30	-	S	V _{DS} =10V, I _D =28A
Gate-Source Leakage Current	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V
Drain-Source Leakage Current(T _j =25°C)	I _{DSS}	-	-	1	uA	V _{DS} =25V, V _{GS} =0
Drain-Source Leakage Current(T _j =150°C)		-	-	25	uA	V _{DS} =20V, V _{GS} =0
Static Drain-Source On-Resistance ³	R _{DS(ON)}	-	4.5	6	mΩ	V _{GS} =10V, I _D =30A
		-	7	9		V _{GS} =4.5V, I _D =30A
Total Gate Charge ³	Q _g	-	16.8	-	nC	I _D =28A V _{DS} =20V V _{GS} =5V
Gate-Source Charge	Q _{gs}	-	6.0	-		
Gate-Drain ("Miller") Change	Q _{gd}	-	4.9	-		
Turn-on Delay Time ³	T _{d(on)}	-	15.1	-	ns	V _{DS} =15V I _D =28A V _{GS} =10V R _G =3.3Ω R _D =0.53Ω
Rise Time	T _r	-	4	-		
Turn-off Delay Time	T _{d(off)}	-	45.2	-		
Fall Time	T _f	-	7.6	-		
Input Capacitance	C _{iss}	-	2326	-	pF	V _{GS} =0V V _{DS} =25V f=1.0MHz
Output Capacitance	C _{oss}	-	331	-		
Reverse Transfer Capacitance	C _{rss}	-	174	-		

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward On Voltage ³	V _{SD}	-	-	1.5	V	I _S =20A, V _{GS} =0V, T _j =25°C
Continuous Source Current (Body Diode)	I _S	-	-	55	A	V _D = V _G =0V, V _S =1.5V

Notes: 1. Pulse width limited by safe operating area.

2. Staring T_j=25°C, V_{DD}=20V, L=0.1mH, R_G=25Ω, I_{AS}=10A.

3. Pulse width ≤ 300us, duty cycle ≤ 2%.

Characteristics Curve

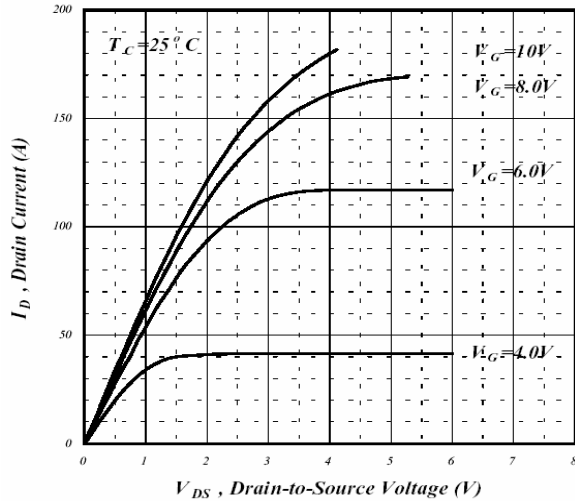


Fig 1. Typical Output Characteristics

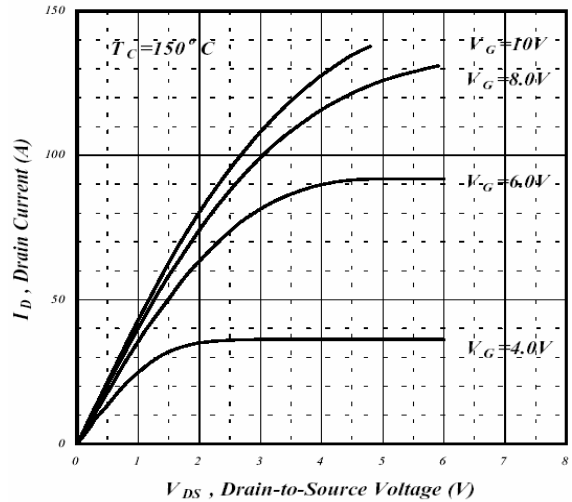


Fig 2. Typical Output Characteristics

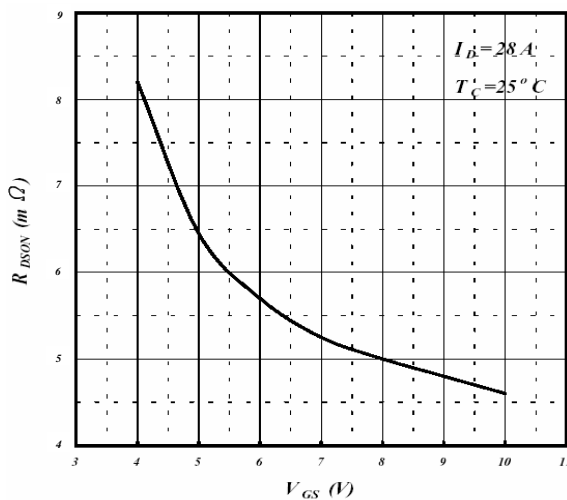


Fig 3. On-Resistance v.s. Gate Voltage

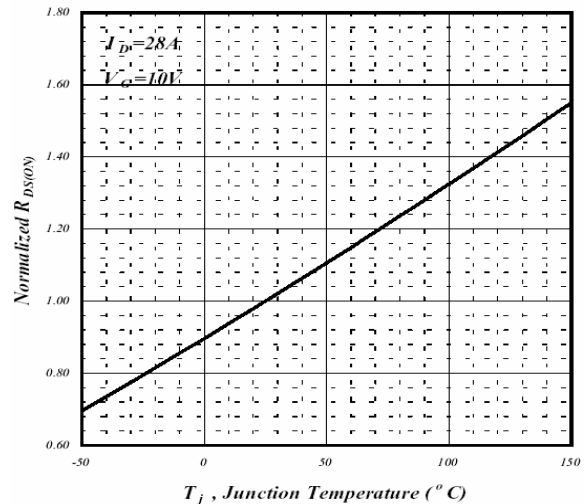


Fig 4. Normalized On-Resistance v.s. Junction Temperature

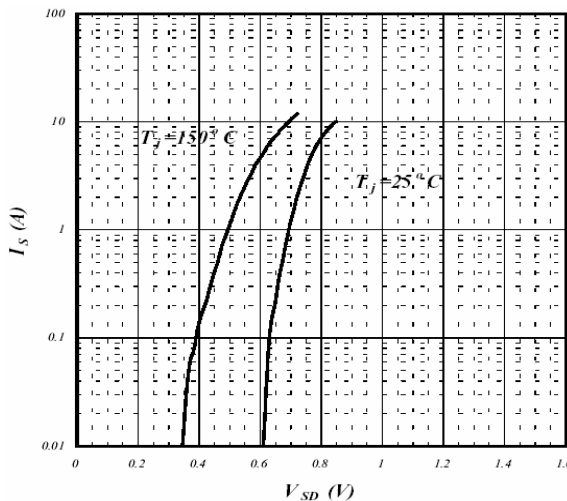


Fig 5. Forward Characteristics of Reverse Diode

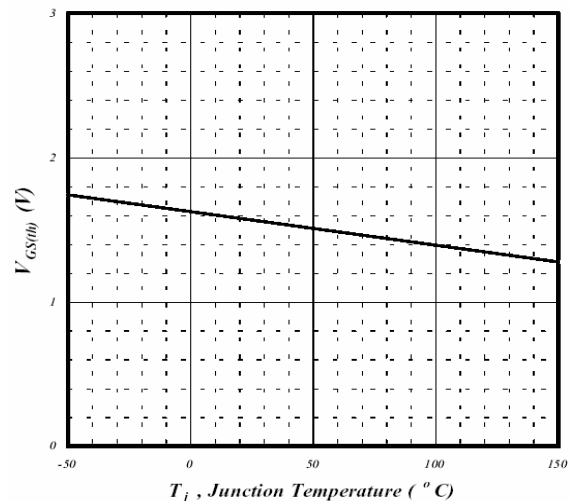
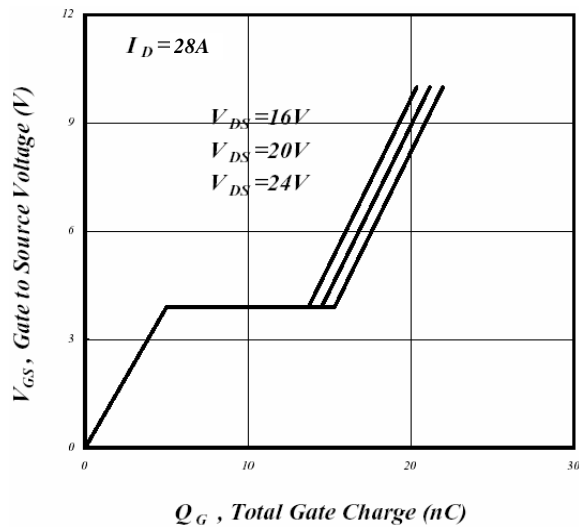


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



Q_G , Total Gate Charge (nC)
Fig 7. Gate Charge Characteristics

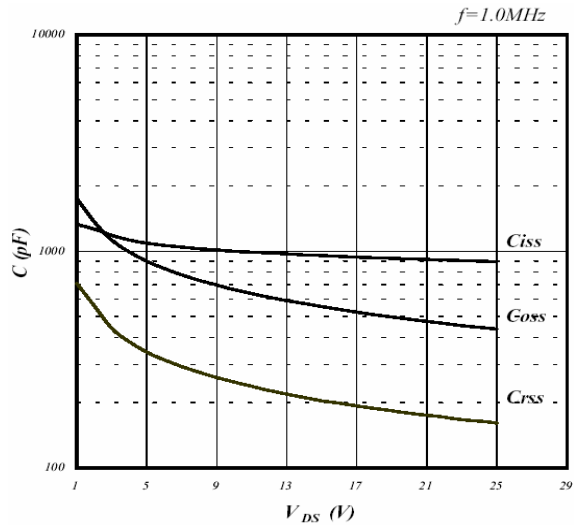


Fig 8. Typical Capacitance Characteristics

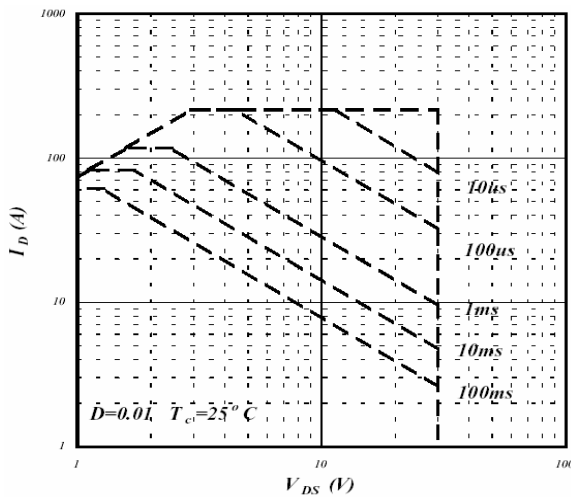


Fig 9. Maximum Safe Operating Area

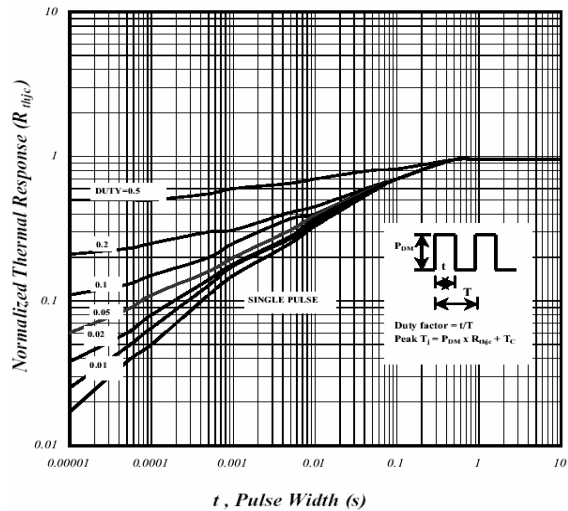


Fig 10. Effective Transient Thermal Impedance

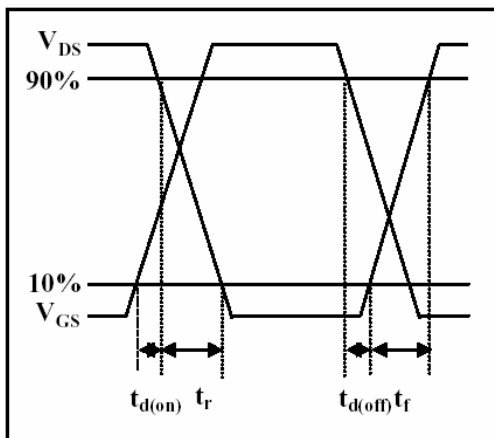


Fig 11. Switching Time Waveform

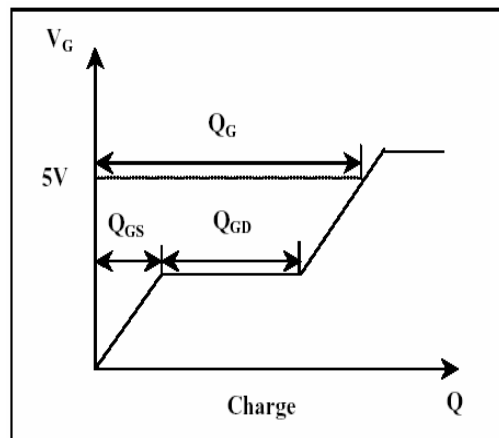


Fig 12. Gate Charge Waveform

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